

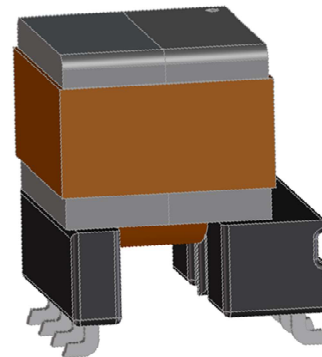
Gate Drive Transformers for high speed SiC MOSFET and IGBT (EP7 small SMD package) 03-38D

Main features and benefits

- Up to 6W output power
- Input voltage 9V to 18V (UT38B61S~64S), 18 to 36V (UT38B65S~66S)
- Flyback switching frequency : 350kHz
- Dielectric insulation up to 4KVac
- Low Interwinding Capacitance and High Common-Mode Transient Immunity (CMTI)
- Basic Insulation for a working voltage 568Vrms / 800Vpk ,Compliance with IEC62368-1/IEC61558-2-16
- Design for Ti's LM5180 and ADI's LT8302 IC chipset applications.
- Common control voltage for SiC MOSFETs
- Operating Temperature: -40°C to +130°C..

Applications

- Industrial drives
- AC motor inverters
- HEV/EV charging station
- Battery chargers
- Solar inverters
- Data centers
- Uninterruptible power supplies
- Active power factor correction
- SiC MOSFET based power converter



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